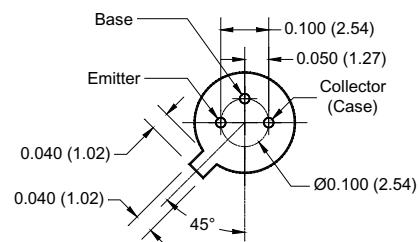
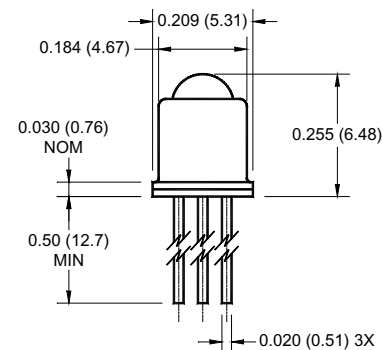
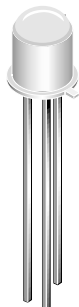


Hermetic Silicon Photosensors

TO-18 Detector Package (Convex Lens)



Part Number	V _{CE} (V)	Test Conditions		I _C (ON) (mA)		BV _{CEO} (V) max	I _{CEO} @ 10 V V _{CE} (nA) max	Sensor Type
		E _o (mW/cm ²)	λ _p (nm)	min	max			
BPW36	5	0.5	940 GaAs	1.00	-	30	100	Phototransistor
BPW37	5	0.5	940 GaAs	0.50	-	30	100	Phototransistor
L14G1	5	0.5	940 GaAs	1.00	-	30	100	Phototransistor
L14G2	5	0.5	940 GaAs	0.50	-	30	100	Phototransistor
L14G3	5	0.5	940 GaAs	2.00	-	30	100	Phototransistor
L14P1	5	0.5	940 GaAs	6.50	-	30	100	Phototransistor
L14P2	5	0.5	940 GaAs	13.0	-	30	100	Phototransistor

Part Number	V _{CE} (V)	Test Conditions		I _C (ON) (mA)		BV _{CEO} (V) max	I _{CEO} @ 12 V V _{CE} (nA) max	Sensor Type
		E _o (mW/cm ²)	λ _p (nm)	min	max			
BPW38	5	0.05	940 GaAs	3.00	-	25	100	Photodarlington
L14F1	5	0.05	940 GaAs	3.00	-	25	100	Photodarlington
L14F2	5	0.05	940 GaAs	1.00	-	25	100	Photodarlington

All dimensions are in inches (millimeters)

PARAMETER	BPW38, L14F	L14G/P, BPW36/7
	Absolute Maximum Ratings	
Temperature		
T _{OPR}	-65 to +125°C	-65 to +125°C
T _{STG}	-65 to +150°C	-65 to +150°C
T _{SOL-H}	240°C for 5 sec	240°C for 5 sec
T _{SOL-F}	260°C for 10 sec	260°C for 10 sec
Sensor		
V _{CEO}	25 V	30 V
V _{CBO}	25 V	40 V
V _{EBO}	12.0 V	5.0 V
P _D	300 mW	300 mW